

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON) \max}$	$I_D \max$ $T_A = +25^\circ\text{C}$
60V	$3\Omega @ V_{GS} = 10V$	300mA

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

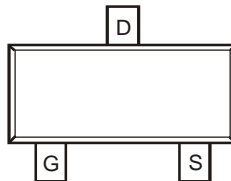
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 ^{e3}
- Weight: 0.008 grams (approximate)

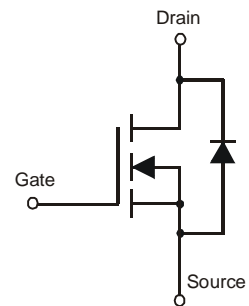
SOT23



Top View



Top View
Pin Out Configuration



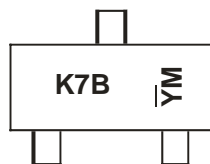
Equivalent Circuit

Ordering Information (Note 4)

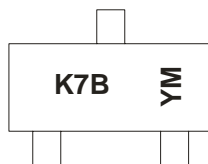
Part Number	Case	Packaging
2N7002E-7-F	SOT23	3,000/Tape & Reel
2N7002E-13-F	SOT23	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



Chengdu A/T Site



Shanghai A/T Site

K7B = Product Type Marking Code
 YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)
 YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)
 Y or Y= Year (ex: A = 2013)
 M = Month (ex: 9 = September)

Date Code Key

Year	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	P	R	S	T	U	V	W	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	60	V
Drain-Gate Voltage R _{GS} ≤ 1.0MΩ			V _{DGR}	60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Pulsed				±40	
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	250	mA
		T _A = +70°C		200	
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	300	mA
		T _A = +70°C		240	
Maximum Body Diode Forward Current (Note 6)			I _S	500	mA
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	800	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation	(Note 5)	P _D	370	mW
	(Note 6)		540	
Thermal Resistance, Junction to Ambient	(Note 5)	R _{θJA}	348	°C/W
	(Note 6)		241	
Thermal Resistance, Junction to Case	(Note 6)	R _{θJC}	91	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to 150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	70	—	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0	μA	V _{DS} = 60V, V _{GS} = 0V
@ T _C = +125°C				500		
Gate-Body Leakage	I _{GSS}	—	—	±10	nA	V _{GS} = ±15V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	1.0	—	2.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.6	3	Ω	V _{GS} = 10V, I _D = 250mA V _{GS} = 4.5V, I _D = 200mA
@ T _J = +25°C			2.0	4		
On-State Drain Current	I _{D(ON)}	0.8	1.0	—	A	V _{GS} = 10V, V _{DS} = 7.5V
Forward Transconductance	g _{FS}	80	—	—	mS	V _{DS} = 10V, I _D = 0.2A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	22	50	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	11	25	pF	
Reverse Transfer Capacitance	C _{rss}	—	2.0	5.0	pF	
Gate resistance	R _g	—	120	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	223	—	pC	V _{DS} = 10V, I _D = 250mA
Gate-Source Charge	Q _{gs}	—	82	—	pC	
Gate-Drain Charge	Q _{gd}	—	178	—	pC	
SWITCHING CHARACTERISTICS (Note 8)						
Turn-On Delay Time	t _{D(ON)}	—	7.0	20	ns	V _{DD} = 30V, I _D = 0.2A, R _L = 150Ω, V _{GEN} = 10V, R _{GEN} = 25Ω
Turn-Off Delay Time	t _{D(OFF)}	—	11	20	ns	

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 - Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

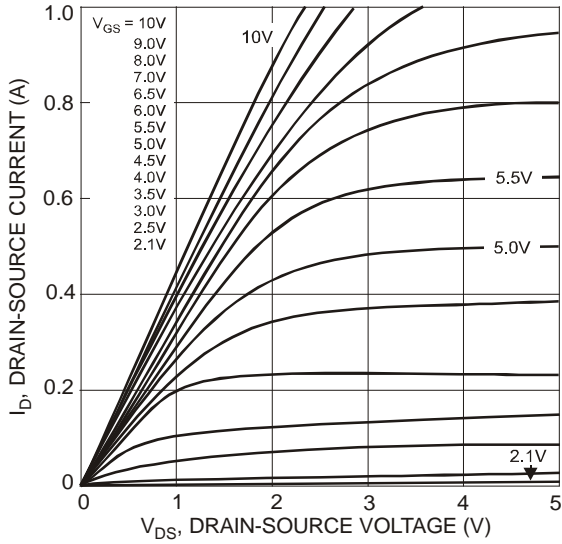


Fig. 1 On-Region Characteristics

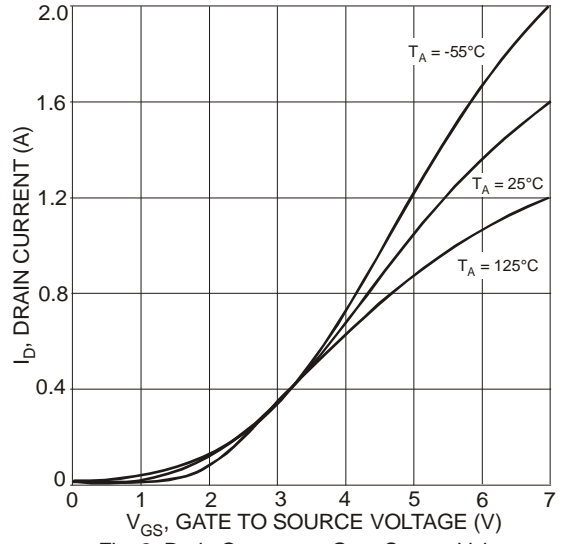


Fig. 2 Drain Current vs. Gate-Source Voltage

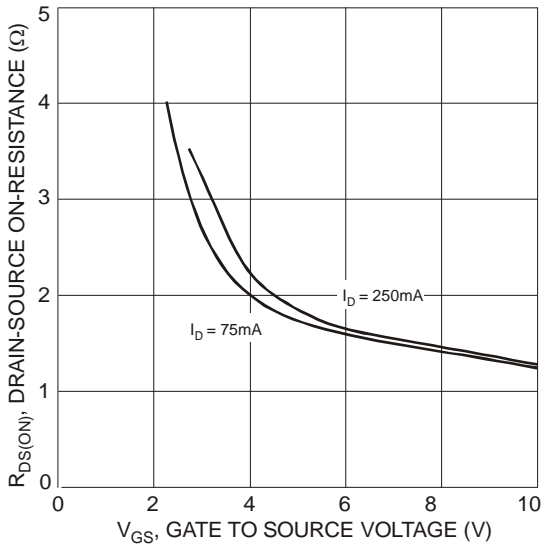


Fig. 3 On Resistance vs. Gate-Source Voltage

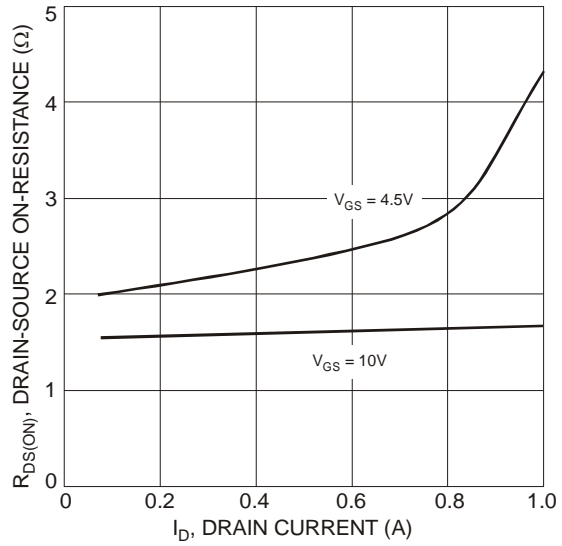


Fig. 4 On Resistance vs. Drain Current

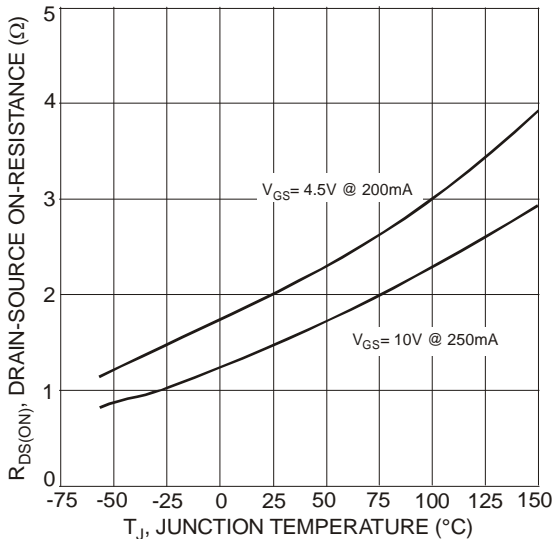


Fig. 5 On-Resistance vs. Junction Temperature

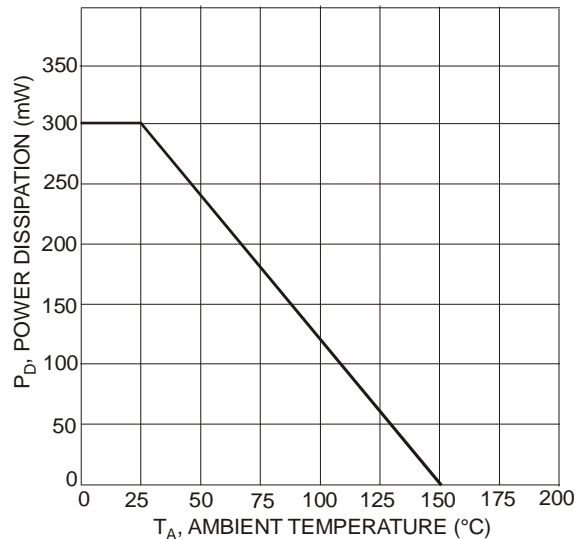
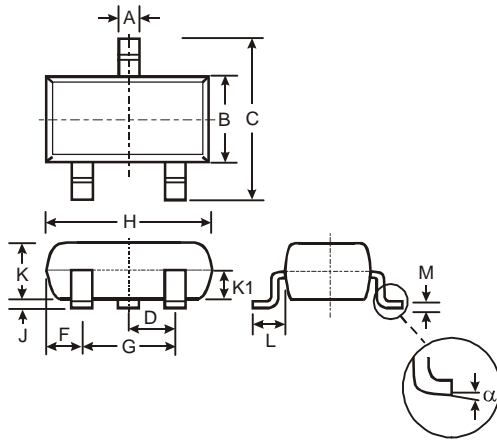


Fig. 6 Max Power Dissipation vs. Ambient Temperature

Package Outline Dimensions

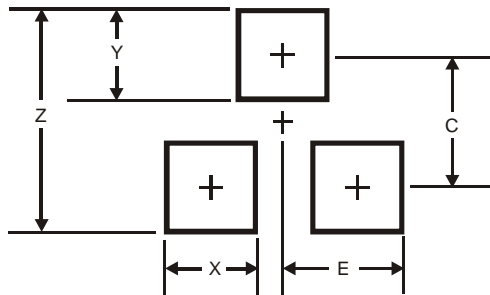
Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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